

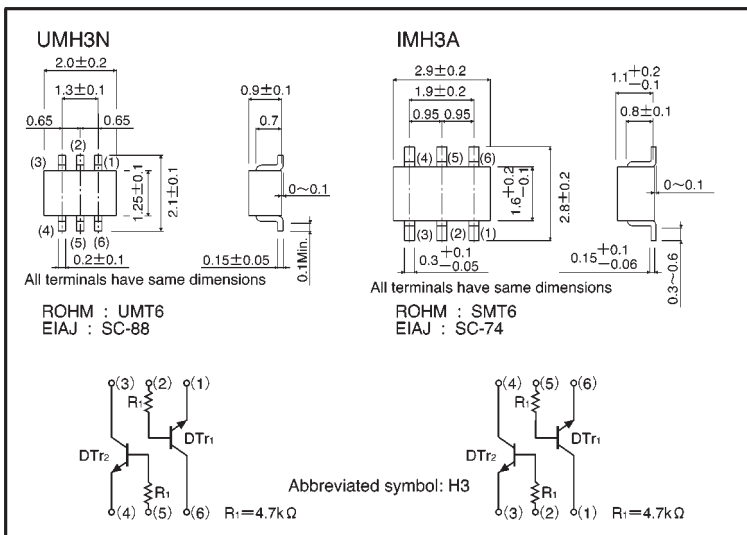
UMH3N / IMH3A

● External dimensions (Units: mm)

- ## ● Structure

Epitaxial planar type
NPN silicon transistor

The following characteristics apply to both DTr₁ and DTr₂.



Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage		V_{CEO}	50	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I_C	100	mA
Collector power dissipation	UMH3N	P_C	150 (TOTAL)	mW
	IMH3A		300 (TOTAL)	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	-55~+150	°C

*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=50V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_E=5mA/0.25mA$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE}=5V, I_C=1mA$
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=10mA, I_E=-5mA, f=100MHz$ *
Input resistance	R_i	3.29	4.7	6.11	k Ω	—

* Transition frequency of the device

●Packaging specifications

Part No.	Packaging type	Taping	
	Code	TN	T110
	Basic ordering unit (pieces)	3000	3000
UMH3N		○	—
IMH3A		—	○

●Electrical characteristic curves

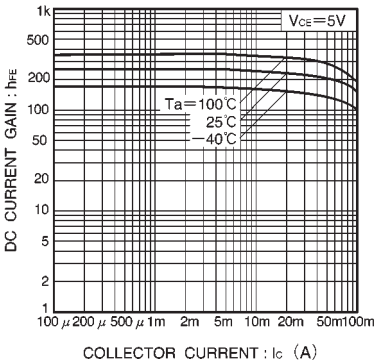


Fig.1 DC current gain vs. collector current

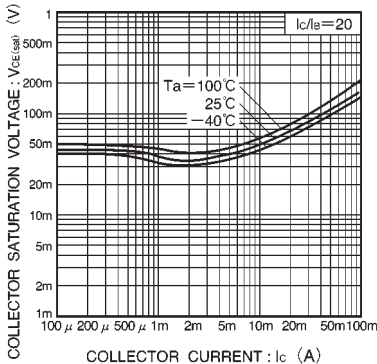


Fig.2 Collector-emitter saturation voltage vs. collector current